



A Product Line of Diodes Incorporated

ZXTN2010Z

### 60V NPN LOW SATURATION MEDIUM POWER TRANSISTOR IN SOT89

#### Features

- BV<sub>CEO</sub> > 60V
- High current capability Max Continuous Current I<sub>C</sub> = 5A
- $R_{SAT} = 30m\Omega$  for a low equivalent On-Resistance
- Low saturation voltage V<sub>CE(sat)</sub> < 65mV @ I<sub>C</sub> = 1A
- h<sub>FE</sub> specified up to 10A for high current gain hold up
- Complementary PNP type: ZXTP2012Z
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

SOT89

• PPAP capable (Note 4)

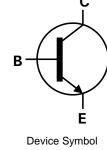
# Mechanical Data

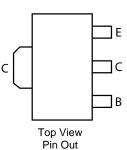
- Case: SOT89
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <sup>(3)</sup>
- Weight: 0.05 grams (Approximate)

### Application

- Emergency lighting circuits
- Motor driving (including DC fans)
- Backlight inverters
- Power switches
- Gate driving MOSFETs and IGBTs

Top View





## Ordering Information (Note 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN2010ZTA	AEC-Q101	851	7	12	1,000
ZXTN2010Z-13R	AEC-Q101	851	13	12	4,000
ZXTP2012ZQTA	Automotive	851	7	12	1,000

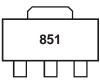
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and</li>

<1000ppm antimony compounds. 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally

the same, except where specified. 5. For packaging details, go to our website at http://www.diodes.com

## **Marking Information**



ZXTN2010Z Datasheet Number: DS33661 Rev. 3 - 2 851 = Product Type Marking Code





**ZXTN2010Z** 

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	150	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ι <sub>C</sub>	5	A
Peak Pulse Current	I <sub>CM</sub>	20	A

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) Linear derating factor	PD	1.5 12	W mW/°C
Power Dissipation (Note 7) Linear derating factor	PD	2.1 16.8	W mW/°C
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	83	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>0JA</sub>	60	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R <sub>0JL</sub>	3.23	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

Notes: 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; device measured when operating in steady state condition.

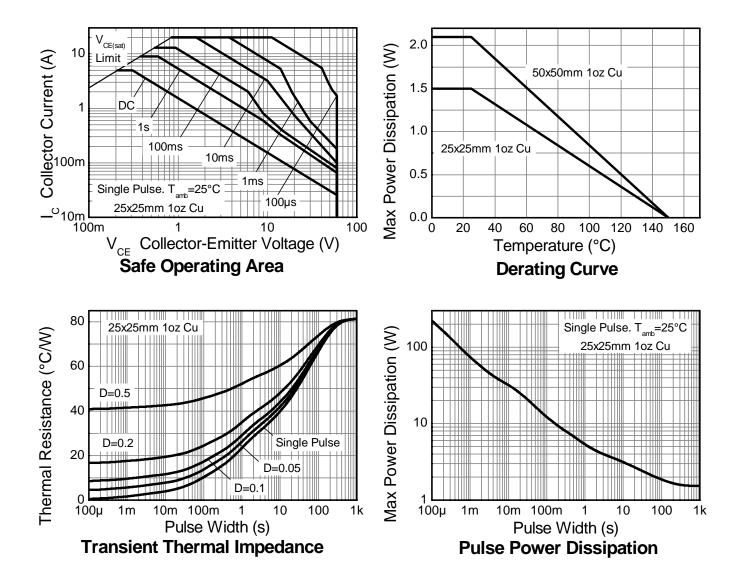
7. Same as note (6), except the device is mounted on 50mm X 50mm single sided 1oz weight copper.

8. Thermal resistance from junction to solder-point (on the exposed collector pad).





## Thermal Characteristics and Derating Information







Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	150	190	-	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Notes 9)	BV <sub>CER</sub>	150	190	-	V	$I_{C} = 1\mu A, R_{B} \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Notes 9)	BV <sub>CEO</sub>	60	80	-	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.1	-	V	$I_{E} = 100 \mu A$
Collector Cutoff Current	I <sub>CBO</sub>	-	< 1	50 500	nA nA	V <sub>CB</sub> = 120V V <sub>CB</sub> = 120V, T <sub>A</sub> = +100°C
Collector Cutoff Current	I <sub>CER</sub> R ≤1kΩ	-	< 1	100 500	nA nA	V <sub>CB</sub> = 120V V <sub>CB</sub> = 120V, T <sub>A</sub> = +100°C
Emitter Cutoff Current	I <sub>EBO</sub>	-	< 1	10	nA	$V_{EB} = 6V$
	hfe	100	200	-		$I_{C} = -10mA, V_{CE} = -1V$
DC current transfer Static ratio (Notes 9)		100	200	300		$I_{C} = -2A, V_{CE} = -1V$
De current transfer Static Tatio (Notes 9)		55	105	-		$I_{C} = -5A, V_{CE} = -1V$
		20	40	-		$I_{C} = -10A, V_{CE} = -1V$
	V <sub>CE(sat)</sub>	-	17	30	mV	$I_{C} = 100 \text{mA}, I_{B} = 5 \text{mA}$
		-	35	55		$I_{C} = 1A, I_{B} = 100mA$
Collector-Emitter Saturation Voltage (Notes 9)		-	40	65		$I_{C} = 1A, I_{B} = 50mA$
		-	90	125		$I_{C} = 2A, I_{B} = 50mA$
		-	170	230		$I_{C} = 6A, I_{B} = 300mA$
Base-Emitter Saturation Voltage (Notes 9)	V <sub>BE(sat)</sub>	-	970	1100	mV	$I_{C} = 6A, I_{B} = 300mA$
Base-Emitter Turn-on Voltage (Notes 9)	V <sub>BE(on)</sub>	-	910	1050	mV	$I_{C} = 6A, V_{CE} = 1V$
Transitional Frequency	f <sub>T</sub>	-	130	-	MHz	$I_C = 100 \text{mA}, V_{CE} = 10 \text{V},$ f = 50MHz
Output capacitance	C <sub>obo</sub>	-	31	-	pF	$V_{CB} = 10V, f = 1MHz,$
Switching Time	t <sub>ON</sub>	42		2	ns	$V_{CC} = 10V, I_C = 1A,$
	t <sub>OFF</sub>	- [	760	-	115	$I_{B1} = I_{B2} = 100 \text{mA}$

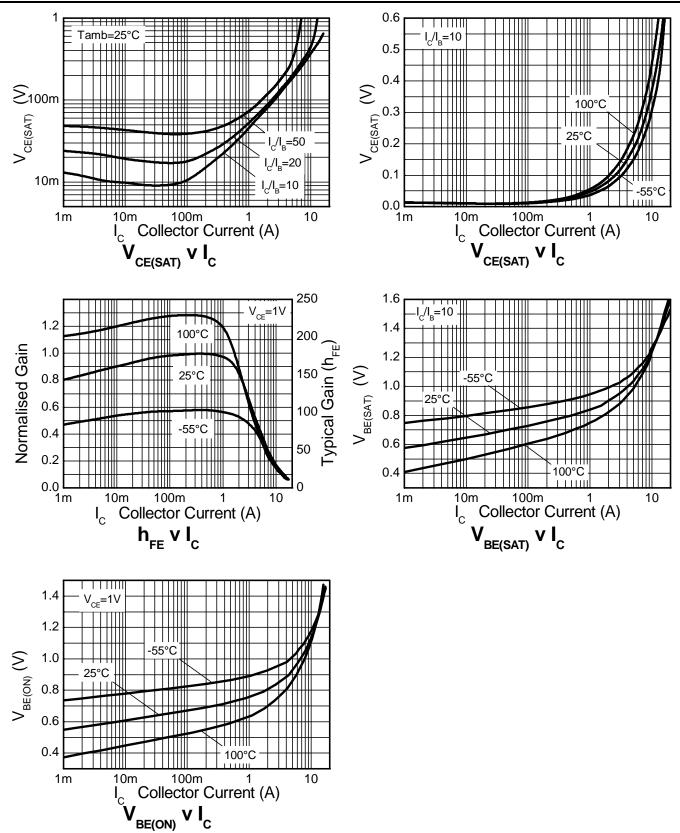
9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%. Notes:





ETEX

## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

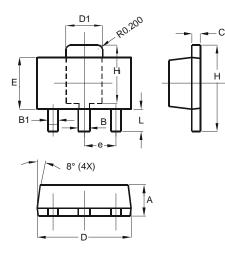






## **Package Outline Dimensions**

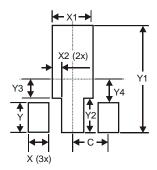
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT89				
Dim	Min Max			
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
С	0.35	0.44		
D	4.40	4.60		
D1	1.62	1.83		
ш	2.29	2.60		
e	1.50 Typ			
Н	3.94	4.25		
H1	2.63	2.93		
L	0.89	1.20		
All Dimensions in mm				

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500





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